

**Silicon NPN Power Transistors**

**2SC3557**

**DESCRIPTION**

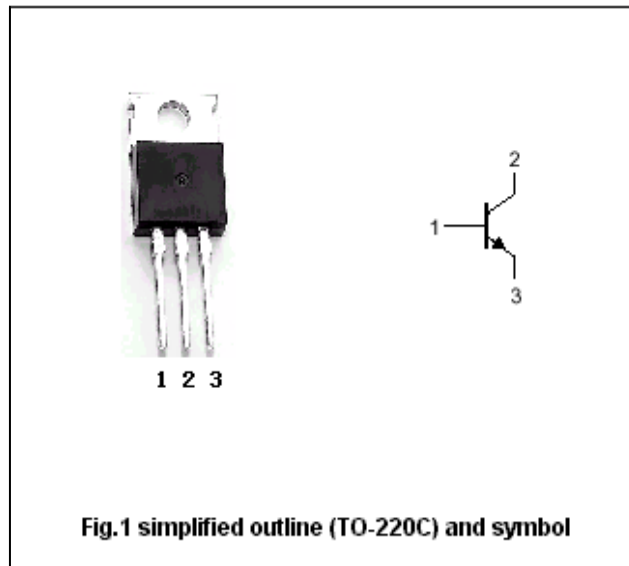
- With TO-220C package
- Low collector saturation voltage

**APPLICATIONS**

- For medium power linear and switching applications

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



**Absolute maximum ratings (Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	80	V
$V_{CEO}$	Collector-emitter voltage	Open base	80	V
$V_{EBO}$	Emitter-base voltage	Open collector	5	V
$I_C$	Collector current		4	A
$P_C$	Collector power dissipation	$T_C=25^{\circ}C$	40	W
$T_j$	Junction temperature		150	$^{\circ}C$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}C$

## Silicon NPN Power Transistors

## 2SC3557

## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =30mA; I <sub>B</sub> =0	80			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =3A; I <sub>B</sub> =0.3 A			1.5	V
I <sub>CEO</sub>	Collector cut-off current	V <sub>CE</sub> =60V; I <sub>B</sub> =0			0.5	mA
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =80V; I <sub>E</sub> =0			0.1	mA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			0.1	mA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =0.2A ; V <sub>CE</sub> =1V	150			

Silicon NPN Power Transistors

2SC3557

PACKAGE OUTLINE

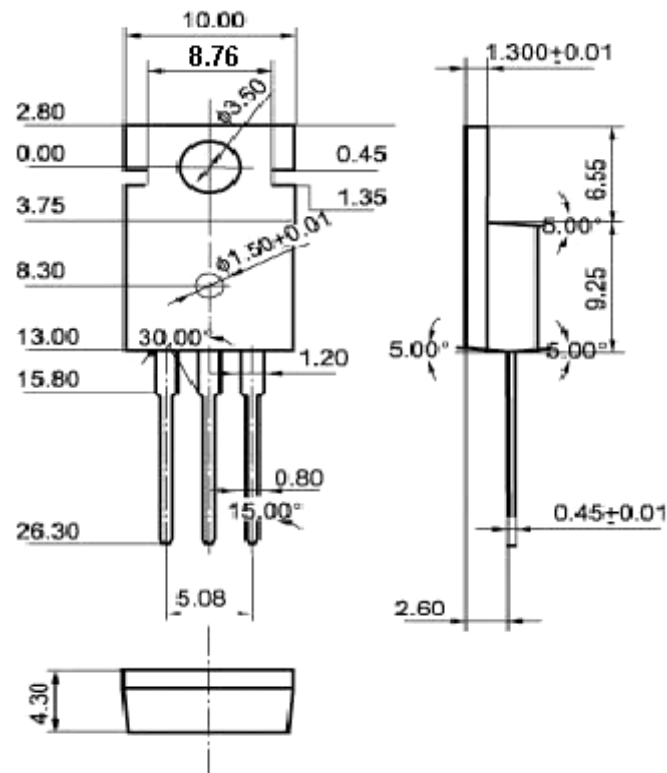


Fig.2 Outline dimensions (unindicated tolerance: ±0.10 mm)